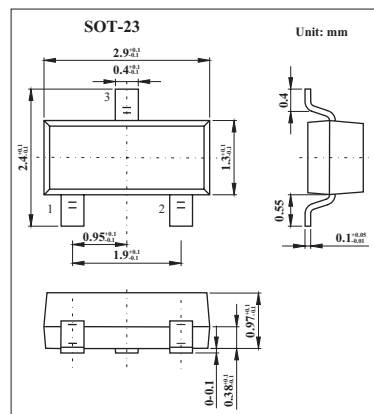


BAR14;BAR15;BAR16

■ Features

- RF switch
- RF attenuator for frequencies above 10 MHz
- Low distortion factor
- Long-term stability of electrical characteristics



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage	V _R	100	V
Forward current	I _F	140	mA
Total power dissipation, T _s ≤ 65°C ¹⁾	P _{tot}	250	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C
Operating temperature range	T _{op}	-55 to +150	°C
Junction - ambient ¹⁾	R _{thJA}	≤ 500	K/W
Junction - soldering point	R _{thJS}	≤ 340	

Note

1. Package mounted on alumina 15 mm × 16.7 mm × 0.7 mm.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse current	V _R	V _R = 50 V			100	nA
		V _R = 100 V			1	μA
Forward voltage	V _F	I _F = 100 mA		1.05		V
Diode capacitance	C _T	V _R = 50 V, f = 1 MHz		0.25	0.5	pF
		V _R = 0, f = 100 MHz		0.2		
Forward resistance	r _f	I _F = 0.01 mA, f = 100 MHz		2800		Ω
		I _F = 0.1 mA, f = 100 MHz		380		
		I _F = 1 mA, f = 100 MHz		45		
		I _F = 10 mA, f = 100 MHz		7		
Zero bias conductance	g _p	V _R = 0, f = 100 MHz		50		μS
Charge carrier life time	t _{rr}	I _F = 10 mA, I _R = 6 mA	0.7	1		μS

■ Marking

Type	BAR14	BAR15	BAR16
Marking	L7	L8	L9